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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/767,786	01/29/2004	Koichi Ohto	17408	7289
23389	7590	07/25/2005	EXAMINER	
SCULLY SCOTT MURPHY & PRESSER, PC 400 GARDEN CITY PLAZA SUITE 300 GARDEN CITY, NY 11530			NADAV, ORI	
			ART UNIT	PAPER NUMBER
			2811	

DATE MAILED: 07/25/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

HA

Office Action Summary

Application No.

10/767,786

Applicant(s)

OHTO ET AL.

Examiner

Ori Nadav

Art Unit

2811

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 11 July 2005.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-82 is/are pending in the application.
- 4a) Of the above claim(s) 27-82 is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-26 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☒ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 29 January 2004 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All b) ☐ Some * c) ☐ None of:
1. ☒ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☒ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date 3/22/04.
- 4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____.

Art Unit: 2811

DETAILED ACTION

Election/Restrictions

Applicant's election without traverse of claims 1-38 and the embodiment of figure 2 (claims 1-26) in the reply filed on 7/11/2005 is acknowledged.

Specification

The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

Claim Objections

Claims 1-26 are objected to because of the following informalities: In claim 1, line 4, the term "wring" should read "wiring". Appropriate correction is required.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1, 3-9, 14-21 and 26 are rejected under 35 U.S.C. 103(a) as being unpatentable over Suzuki et al. (6,514,855) in view of Baklanov et al. (6,593,251), Matsuki et al. (6,559,520) and Shioya et al. (6,852,651).

Art Unit: 2811

Suzuki et al. teach in figure 2F and related text a semiconductor device comprising;

a semiconductor substrate 1; and

a multi-layered wiring arrangement provided on said semiconductor substrate, said multi-layered wiring arrangement including at least one insulating layer structure having a metal wiring constitution formed therein,

wherein said insulating layer structure includes a first SiOCH layer 12, a second SiOCH layer 13 formed on said first SiOCH layer, and a silicon dioxide (SiO₂) layer 17 formed on said second SiOCH layer, and said second SiOCH layer features a carbon (c) density lower than that of said first SiOCH layer (column 5, lines 17-19).

Suzuki et al. do not teach a silicon dioxide (SiO₂) layer formed on said second SiOCH layer, wherein said second SiOCH layer includes a hydrogen (H) density lower than that of said first SiOCH layer, and an oxygen (O) density higher than that of said first SiOCH layer.

Suzuki et al. teach a second SiOCH layer being a porous SiOCH layer.

Baklanov et al. teach an improved porous SiOCH layer having specific concentration of elements.

Matsuki et al. teach a porous SiOCH layer having higher oxygen concentration

Shioya et al. teach in figure 9A a silicon dioxide (SiO₂) layer 35 formed on a SiOCH layer.

It would have been obvious to a person of ordinary skill in the art at the time the invention was made to form a silicon dioxide (SiO₂) layer on said second SiOCH layer, wherein said second SiOCH layer includes a hydrogen (H) density lower than that of

Art Unit: 2811

said first SiOCH layer, and an oxygen (O) density higher than that of said first SiOCH layer, in order to provide better protection to the device, and in order to improve the characteristics of the porous SiOCH layer, respectively. Note that substitution of materials is not patentable even when the substitution is new and useful. *Safetran Systems Corp. v. Federal Sign & Signal Corp.* (DC NIII, 1981) 215 USPQ 979.

Regarding claims 3-9, 14-21 and 26, Suzuki et al. and Shioya et al. teach an insulating layer structure has a trench pattern formed therein, and said metal wiring constitution comprises a metal wiring pattern buried in said trench pattern, wherein said metal wiring pattern is made of copper (Cu), and a barrier metal layer is formed on wall faces defining said trench pattern to thereby prevent diffusion of copper atoms from said copper wiring pattern into said insulating layer structure,

wherein said barrier metal layer has a single-layered structure, which is formed of one selected from a group consisting of titanium, a titanium compound, tantalum, and a tantalum compound,

wherein said titanium compound is either titanium nitride (TiN) or titanium silicon nitride (TiSiN), and a tantalum compound (Ta) is either tantalum nitride (TaN) or tantalum silicon nitride (TaSiN),

wherein said copper wiring pattern contains at least one aluminum,

wherein said insulating layer structure has at least one hole formed therein, and said metal wiring constitution comprises a metal via-plug buried in said hole, and

Art Unit: 2811

wherein a barrier insulating layer on which said first SiOCH layer is formed, and said barrier insulating layer prevents diffusing of copper atoms into said first SiOCH layer when said insulating layer structure is formed on another insulating layer structure having a copper wiring constitution.

Claims 10 and 22 are rejected under 35 U.S.C. 103(a) as being unpatentable over Suzuki et al. (6,514,855), Baklanov et al. (6,593,251), Matsuki et al. (6,559,520) and Shioya et al. (6,852,651), as applied to claims 1, 3, 4, 9, 15, 16 and 21 above, and further in view of Chung (6,890,869).

Suzuki et al., Baklanov et al., Matsuki et al. and Shioya et al. teach substantially the entire claimed structure, as applied to claims 1, 3, 4, 9, 15, 16 and 21 above, except said barrier insulating layer has a single-layered structure comprising either a SiNCH layer or a SiCH layer.

Chung teaches a barrier insulating layer has a single-layered structure comprising either a SiNCH layer or a SiCH layer.

It would have been obvious to a person of ordinary skill in the art at the time the invention was made to use a barrier insulating layer having a single-layered structure comprising either a SiNCH layer or a SiCH layer in prior art's device in order to provide better protection for the device.

Allowable Subject Matter

Claims 2, 11-13 and 23-25 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Reasons for allowance

The following is an examiner's statement of reasons for allowance:

Suzuki et al. (6,514,855), Baklanov et al. (6,593,251), Matsuki et al. (6,559,520) and Shioya et al. (6,852,651) appear to be the closest prior art reference. The prior art of record does not teach or suggest, singularly or in combination, at least the limitation of the specific densities of elements of the SiOCH layers, as recited in claim 2, and a barrier insulating layer having a multi-layered structure comprising a SiCNH layer, and a SiCH or SiOCNH layer formed thereon, as recited in claims 11-13 and 23-25.

Therefore, prior art do not teach or render obviousness the semiconductor structure, as claimed.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Art Unit: 2811

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ori Nadav whose telephone number is 571-272-1660. The examiner can normally be reached between the hours of 7 AM to 4 PM (Eastern Standard Time) Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Stephen Loke can be reached on 571-272-1657. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).



O.N.
7/20/05

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